

# Wei Mi

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/4023872/publications.pdf>

Version: 2024-02-01

22  
papers

565  
citations

687363

13  
h-index

794594

19  
g-index

22  
all docs

22  
docs citations

22  
times ranked

778  
citing authors

#	ARTICLE	IF	CITATIONS
1	Characterization of $\hat{I}^2$ -Ga <sub>2</sub> O <sub>3</sub> thin films on sapphire (0001) using metal-organic chemical vapor deposition technique. Vacuum, 2012, 86, 1850-1854.	3.5	92
2	Structural and optical properties of heteroepitaxial beta Ga <sub>2</sub> O <sub>3</sub> films grown on MgO (100) substrates. Thin Solid Films, 2012, 520, 4270-4274.	1.8	77
3	Structural and optical properties of $\hat{I}^2$ -Ga <sub>2</sub> O <sub>3</sub> films deposited on MgAl <sub>2</sub> O <sub>4</sub> (1 0 0) substrates by metal-organic chemical vapor deposition. Journal of Luminescence, 2014, 146, 1-5.	3.1	56
4	Ultraviolet-green photoluminescence of $\hat{I}^2$ -Ga <sub>2</sub> O <sub>3</sub> films deposited on MgAl <sub>6</sub> O <sub>10</sub> (100) substrate. Optical Materials, 2013, 35, 2624-2628.	3.6	52
5	Synthesis of Large-Area Highly Crystalline Monolayer Molybdenum Disulfide with Tunable Grain Size in a H <sub>2</sub> Atmosphere. ACS Applied Materials & Interfaces, 2015, 7, 22587-22593.	8.0	47
6	Effect of annealing on the properties of Ga <sub>2</sub> O <sub>3</sub> :Mg films prepared on $\hat{I}^2$ -Al <sub>2</sub> O <sub>3</sub> (0001) by MOCVD. Vacuum, 2016, 124, 101-107.	3.5	37
7	Mg-doped $\hat{I}^2$ -Ga <sub>2</sub> O <sub>3</sub> films with tunable optical band gap prepared on MgO (110) substrates by metal-organic chemical vapor deposition. Materials Science in Semiconductor Processing, 2015, 34, 52-57.	4.0	33
8	Transparent conducting tin-doped Ga <sub>2</sub> O <sub>3</sub> films deposited on MgAl <sub>2</sub> O <sub>4</sub> (100) substrates by MOCVD. Ceramics International, 2015, 41, 2572-2575.	4.8	31
9	Influence of annealing on the structural and optical properties of gallium oxide films deposited on c-sapphire substrate. Vacuum, 2019, 167, 6-9.	3.5	24
10	Optoelectronic artificial synapses based on $\hat{I}^2$ -Ga <sub>2</sub> O <sub>3</sub> films by RF magnetron sputtering. Vacuum, 2021, 192, 110422.	3.5	23
11	A solar-blind photodetector based on $\hat{I}^2$ -Ga <sub>2</sub> O <sub>3</sub> film deposited on MgO (100) substrates by RF magnetron sputtering. Vacuum, 2020, 180, 109632.	3.5	22
12	Effect of Sb doping on structural, electrical and optical properties of epitaxial SnO <sub>2</sub> films grown on r-cut sapphire. Journal of Alloys and Compounds, 2014, 586, 426-430.	5.5	17
13	Characterization of Sn-doped $\hat{I}^2$ -Ga <sub>2</sub> O <sub>3</sub> films deposited on MgO (100) substrate by MOCVD. Journal of Materials Science: Materials in Electronics, 2015, 26, 7889-7894.	2.2	16
14	Resistive random access memory based on gallium oxide thin films for self-powered pressure sensor systems. Ceramics International, 2020, 46, 21141-21148.	4.8	14
15	Preparation and characterization of single crystalline In <sub>2</sub> O <sub>3</sub> films deposited on MgO (110) substrates by MOCVD. Ceramics International, 2014, 40, 4203-4206.	4.8	6
16	Effect of oxygen flow ratio on crystallization and structural characteristics of gallium oxide thin films. Ceramics International, 2022, 48, 3751-3756.	4.8	6
17	Synthesis of monoclinic structure gallium oxide film on sapphire substrate by magnetron sputtering. Optoelectronics Letters, 2017, 13, 295-298.	0.8	5
18	Annealing effect on the optical and electronic properties of $\hat{I}^2$ -Ga <sub>2</sub> O <sub>3</sub> /AZO multilayered films. Journal of Materials Science: Materials in Electronics, 2016, 27, 11390-11395.	2.2	4

#	ARTICLE	IF	CITATIONS
19	Effect of electrode materials and annealing on metal-semiconductor contact of Ga <sub>2</sub> O <sub>3</sub> with metal. Optoelectronics Letters, 2020, 16, 118-121.	0.8	3
20	Influence of annealing on the structural, optical and electrical properties of indium oxide films deposited on c-sapphire substrate. Optoelectronics Letters, 2016, 12, 39-42.	0.8	0
21	Performance Optimization of HFO <sub>x</sub> -Based Transparent Resistance Random Access Memory. , 2019, , .		0
22	Gate Tunable Memtransistor based on Monolayer Molybdenum Disulfide. , 2020, , .		0